

ANTICORROSIVE MATERIAL FOR SEMICONDUCTOR FABRICATION

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Inventor: ITOU YUMIKO; AIDA HIROSHI
Applicant: KYOCERA CORP
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Abstract of JP10004083

PROBLEM TO BE SOLVED: To provide an anticorrosive material having a higher corrosion resistance than SiO₂, Al₂O₃, AlN, etc.

SOLUTION: A part of a product to be exposed to a fluoric corrosive gas such as SF₆, CF₄, CHF₃, ClF₃ and HF or its plasma is made from a compd. thin film or single crystal. The product is e.g. a Si wafer clamp ring, upper electrode shield ring, or inner wall of a plasma treating apparatus, etching apparatus, etc., for the semiconductor fabrication. The compd. is an oxide, nitride, carbide or fluoride of 3a elements on the periodic table, e.g. Sc, La, Ce, Eu and Dy.

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